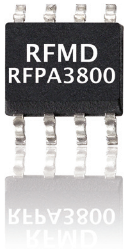
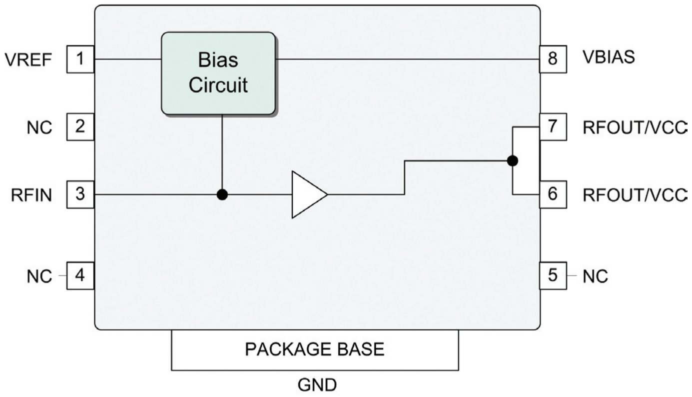
RFMD®

RFPA3800
High Power Amplifier for Applications to 1 GHz



The RFPA3800 is GaAs HBT power amplifier that achieves high OIP3 and P1dB over a range of supply voltages from 5.0 to 7.0 volts. Ideally suited for linear driver applications employing high PAR modulation, the high saturation power of the device also makes it suitable for high power applications that can operate with some degree of compression. Additionally, the relatively low noise figure of approximately 4 dB makes it suitable as a third-stage low noise amplifier for high-performance designs. With simple external matching, the RFPA3800 can achieve good performance over a range of frequencies from 400 to 960 MHz. The device is offered in a plastic SOIC-8 package.

Freq Range (MHz)	*Noise Figure*	*SS Gain (dB)*	*OIP3 (dBm)*	*P1dB (dBm)*	*V_{CC} (V)*	*Part Number*
450	4.5	18.4	48.0	33.5	5.0	RFPA3800
450	4.5	18.0	48.0	36.5	7.0	RFPA3800
900	4.0	14.2	49.0	33.0	5.0	RFPA3800
900	4.0	13.8	49.0	36.0	7.0	RFPA3800



FEATURES

- **High IP3 and compression point with relatively low noise figure**
- **Saturated power >37 dBm with 50% power added efficiency**
- **Low-current power down function**
- **Adjustable bias current**
- **Supply voltage from 3.6 to 7.0 volts**

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